

The BFY 56 is an NPN silicon PLANAR epitaxial transistor designed primarily for amplifier and switching applications over a wide range of voltage and current. These devices feature a useful beta range from 100 μ A to 500 mA and low saturation voltage permitting switching operation at 1 ampere. High collector - to - emitter voltage allows operation to 45 volts.

(T_A = 25°C unless otherwise noted)

ABSOLUTE MAXIMUM RATINGS (1)
(T_A = 25°C unless otherwise noted)

Collector to Base	V_{CB0}	80 V
Collector to Emitter (4)	V_{CE0}	45 V
Emitter to Base	V_{EB0}	5 V

Storage Temperature Range	TSTG	-55°C to +200°C
Junction Temperature	T _J	200°C
Lead Temperature (Soldering, 60 sec. time limit)	T _L	260°C

Dissipation at 25°C Case	Pd	5 W
Temperature		

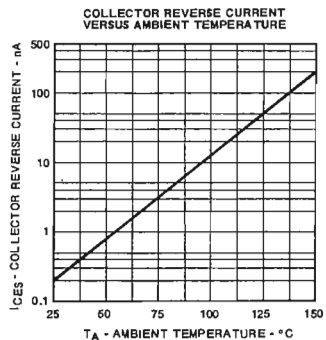
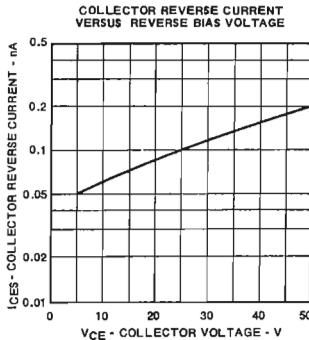
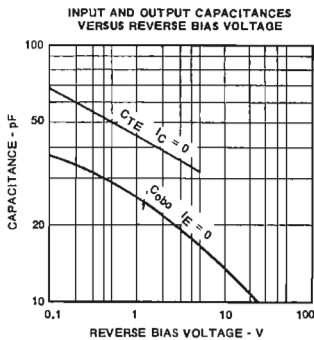
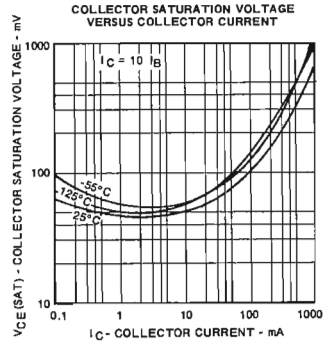
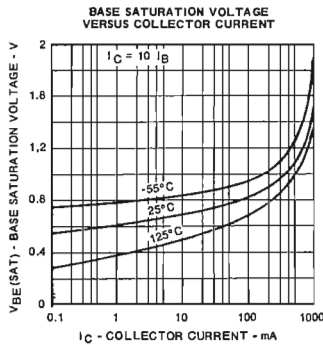
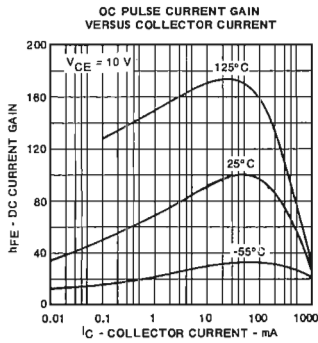
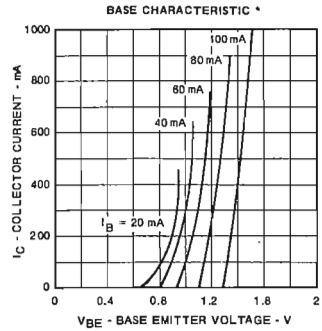
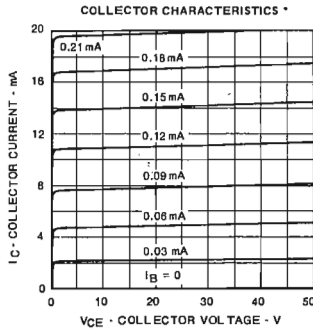
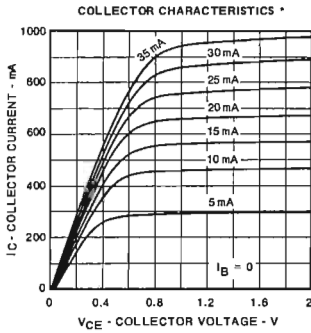
 $P_D = 0.8 \text{ W}$

in accordance with
JEDEC TO-39 OUTLINE



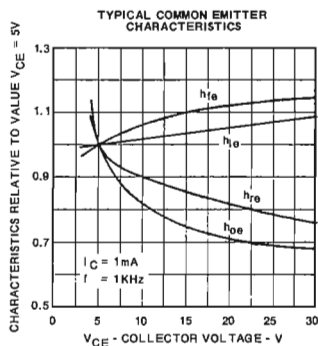
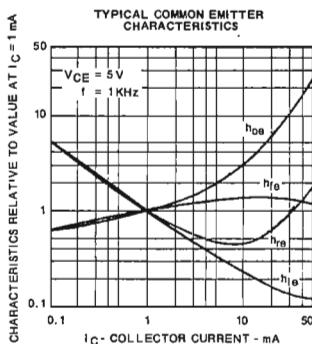
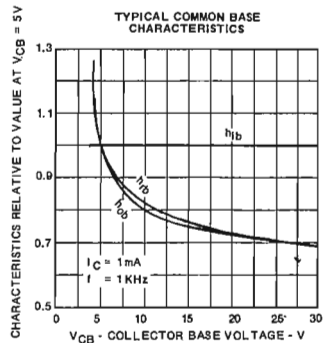
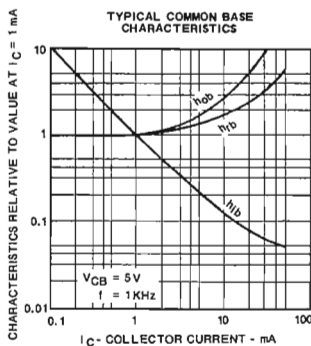
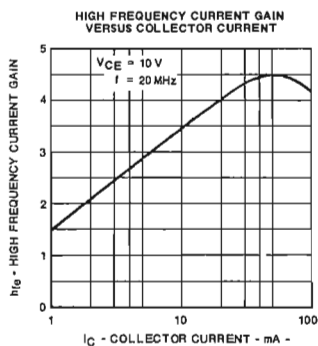
- 153

TYPICAL ELECTRICAL CHARACTERISTICS (25° C free air temperature unless otherwise noted)



* Single family characteristics on Transistor Curve Tracer

TYPICAL ELECTRICAL CHARACTERISTICS (25° C free air temperature unless otherwise noted)



SWITCHING TIME TEST CIRCUIT

